



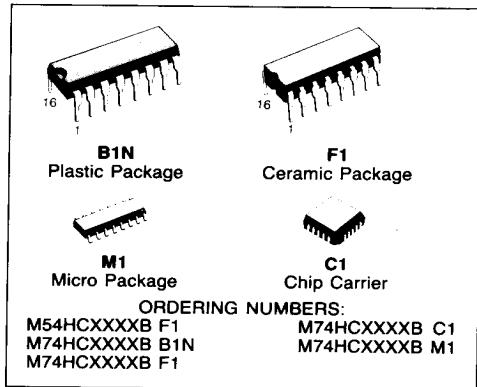
**SGS-THOMSON**  
MICROELECTRONICS

**M54/74HC4049B**

**M54/74HC4050B**

**HC4049B HEX BUFFER/CONVERTER (INVERTER)**  
**HC4050B HEX BUFFER/CONVERTER**

- HIGH SPEED  
 $t_{PD} = 10 \text{ ns (TYP.)}$  at  $V_{CC} = 5V$
- LOW POWER DISSIPATION  
 $I_{CC} = 1 \mu\text{A}$  (MAX.) at  $T_A = 25^\circ\text{C}$
- HIGH NOISE IMMUNITY  
 $V_{NIH} = V_{NIL} = 28\%$   $V_{CC}$  (MIN.)
- OUTPUT DRIVE CAPABILITY  
15 LSTTL LOADS
- SYMMETRICAL OUTPUT IMPEDANCE  
 $|I_{OH}| = I_{OL} = 6 \text{ mA (MIN.)}$
- BALANCED PROPAGATION DELAYS  
 $t_{PLH} = t_{PHL}$
- WIDE OPERATING VOLTAGE RANGE  
 $V_{CC}$  (OPR) = 2V to 6V
- PIN AND FUNCTION COMPATIBLE  
WITH 4049B/4050B



#### DESCRIPTION

The M54/74HC4049B and the M54/74HC4050B are high speed CMOS HEX BUFFER fabricated in silicon gate C<sup>2</sup>MOS technology.

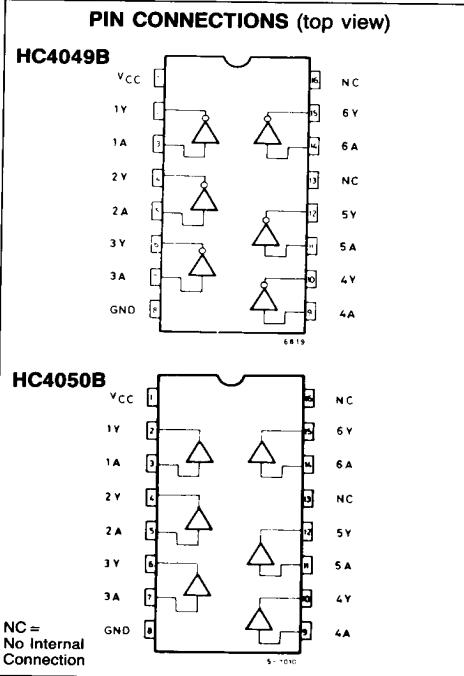
They have the same high speed performance of LSTTL combined with true CMOS low power consumption.

The M54/75HC4049B is an inverting buffer, while the M54/74HC4050B is a non-inverting buffer.

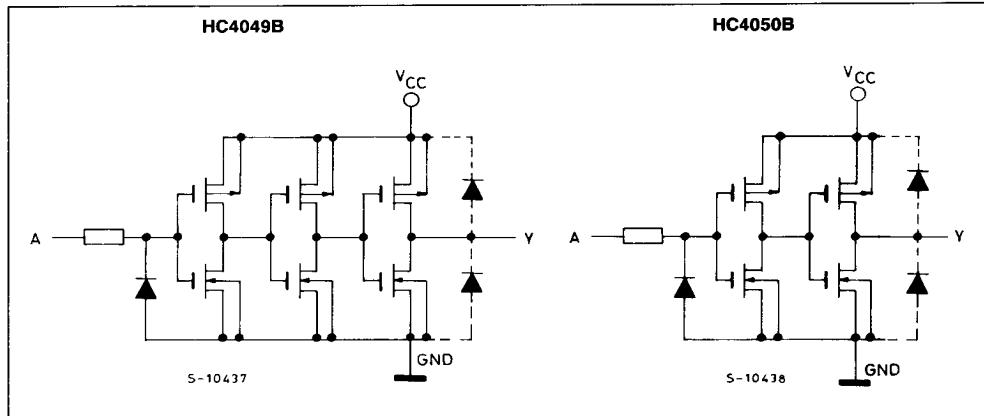
The internal circuit is composed of 3 stage or 2-stage inverters, which provides high noise immunity and a stable output.

Input protection circuits are different from those of the high speed CMOS IC's.

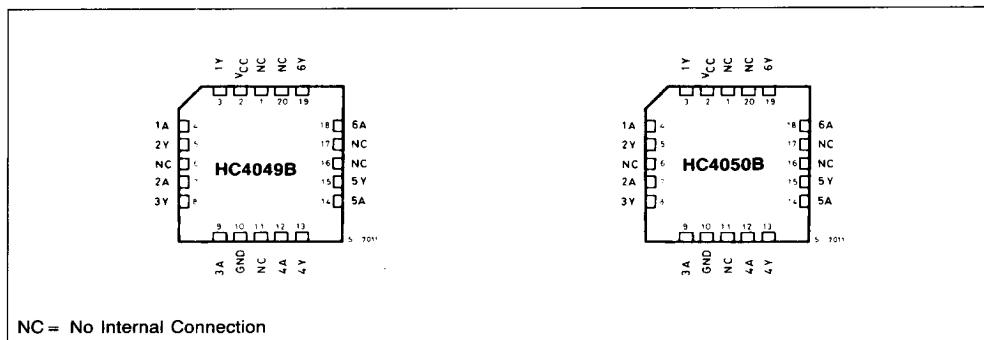
The  $V_{CC}$  side diodes are designed to allow logic-level conversion from high-level voltages (up to 15V) to low-level voltages.



## CIRCUIT SCHEMATIC (Per Gate)



## CHIP CARRIER



## ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V <sub>CC</sub>	Supply Voltage	-0.5 to 7	V
V <sub>I</sub>	DC Input Voltage	-0.5 to 16	V
V <sub>O</sub>	DC Output Voltage	-0.5 to V <sub>CC</sub> + 0.5	V
I <sub>IK</sub>	DC Input Diode Current	± 20	mA
I <sub>OK</sub>	DC Output Diode Current	± 20	mA
I <sub>O</sub>	DC Output Source Sink Current Per Output Pin	± 35	mA
I <sub>CC</sub> or I <sub>GND</sub>	DC V <sub>CC</sub> or Ground Current	± 70	mA
P <sub>D</sub>	Power Dissipation	500 (*)	mW
T <sub>stg</sub>	Storage Temperature	-65 to 150	°C

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied.

(\*) 500 mW: ≈ 65°C derate to 300 mW by 10 mW/°C: 65°C to 85°C.

## RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
$V_{CC}$	Supply Voltage	2 to 6	V
$V_I$	Input Voltage	0 to 15	V
$V_O$	Output Voltage	0 to $V_{CC}$	V
$T_A$	Operating Temperature 74HC Series 54HC Series	-40 to 85 -55 to 125	°C
$t_r, t_f$	Input Rise and Fall Time	$V_{CC} \left\{ \begin{array}{l} 2 \text{ V} \\ 4.5 \text{ V} \\ 6 \text{ V} \end{array} \right. \begin{array}{l} 0 \text{ to } 1000 \\ 0 \text{ to } 500 \\ 0 \text{ to } 400 \end{array}$	ns

## DC SPECIFICATIONS

Symbol	Parameter	$V_{CC}$	Test Condition	$T_A = 25^\circ\text{C}$ 54HC and 74HC			-40 to 85°C 74HC		-55 to 125°C 54HC		Unit
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
$V_{IH}$	High Level Input Voltage	2.0 4.5 6.0		1.5 3.15 4.2	— — —	— — —	1.5 3.15 4.2	— — —	1.5 3.15 4.2	— — —	V
$V_{IL}$	Low Level Input Voltage	2.0 4.5 6.0		— — —	— — —	0.5 1.35 1.8	— — —	0.5 1.35 1.8	— — —	0.5 1.35 1.8	V
$V_{OH}$	High Level Output Voltage	2.0 4.5 6.0 4.5 6.0	$V_I$ $V_{IH}$ or $V_{IL}$	$I_O$ 1.9 4.4 5.9 — —6.0 mA —7.8 mA	2.0 4.5 6.0 — 4.18 5.68	— — — — 4.31 5.8	1.9 4.4 5.9 — 4.13 5.63	— — — — 4.10 5.60	1.9 4.4 5.9 — 4.10 5.60	— — — — — —	V
$V_{OL}$	Low Level Output Voltage	2.0 4.5 6.0 4.5 6.0	$V_I$ $V_{IH}$ or $V_{IL}$	$I_O$ 20 $\mu\text{A}$ — — 6.0 mA 7.8 mA	0.0 0.0 0.0 — 0.17 0.18	0.1 0.1 0.1 — 0.26 0.26	— — — — 0.33 0.33	0.1 0.1 0.1 — 0.33 0.33	— — — — 0.40 0.40	0.1 0.1 0.1 — 0.40 0.40	V
$I_I$	Input Leakage Current	6.0 6.0	$V_I = V_{CC}$ or GND $V_I = 15\text{V}$	— —	— —	$\pm 0.1$ $\pm 0.5$	— —	$\pm 1.0$ $\pm 5$	— —	$\pm 1.0$ $\pm 5$	$\mu\text{A}$
$I_{CC}$	Quiescent Supply Current	6.0	$V_I = V_{CC}$ or GND	—	—	1	—	10	—	20	$\mu\text{A}$

AC ELECTRICAL CHARACTERISTICS ( $V_{CC} = 5\text{V}$ ,  $T_A = 25^\circ\text{C}$ ,  $C_L = 15\text{pF}$ , Input  $t_r = t_f = 6\text{ns}$ )

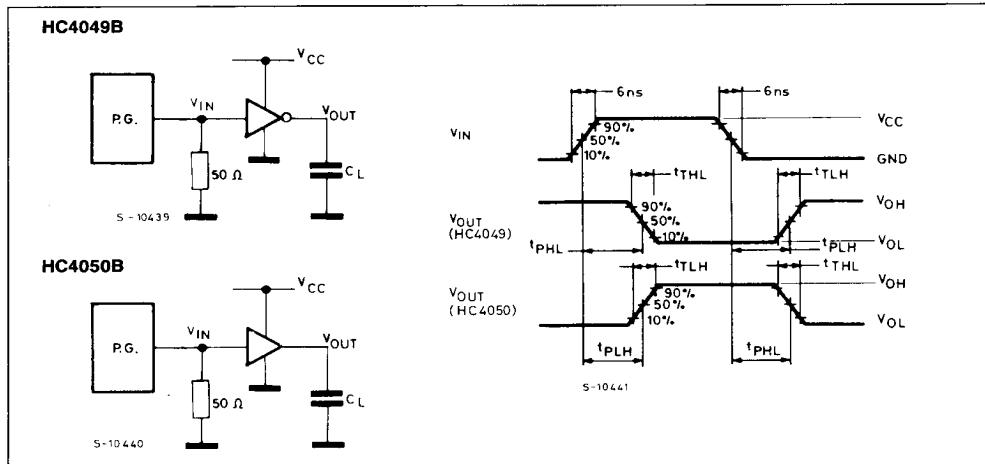
Symbol	Parameter	54HC and 74HC			Unit
		Min.	Typ.	Max.	
$t_{TLH}$ $t_{THL}$	Output Transition Time		7	11	ns
$t_{PLH}$ $t_{PHL}$	Propagation Delay Time		11	16	ns

AC ELECTRICAL CHARACTERISTICS ( $C_L = 50\text{pF}$ , Input  $t_r = t_f = 6\text{ns}$ )

Symbol	Parameter	$V_{CC}$	Test Condition	$T_A = 25^\circ\text{C}$ 54HC and 74HC			-40 to $85^\circ\text{C}$ 74HC		-55 to $125^\circ\text{C}$ 54HC		Unit
				Min.	Typ.	Max.	Min.	Max.	Min.	Max.	
$t_{TLH}$ $t_{THL}$	Output Transition Time	2.0 4.5 6.0		— — —	24 6 5	60 12 10	— — —	75 15 13	— — —	90 18 15	ns
$t_{PLH}$ $t_{PHL}$	Propagation Delay Time	2.0 4.5 6.0		— — —	44 11 9	85 17 14	— — —	105 21 19	— — —	130 26 22	ns
$C_{IN}$	Input Capacitance			—	5	10	—	10	—	10	pF
$C_{PD} (*)$	Power Dissipation Capacitance			—	25	—	—	—	—	—	pF

Note (\*)  $C_{PD}$  is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit)  
 Average operating current can be obtained by the following equation.  
 $I_{CC(\text{opr})} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/4$  (per Gate).

## SWITCHING CHARACTERISTICS TEST CIRCUIT

TEST CIRCUIT  $I_{CC}$  (Opr.)